







## 2N4222, 2N4222A N-Channel JFET

#### **Features**

- InterFET N0032H Geometry
- Typical Noise: 7 nV/vHz
- Low Ciss: 6.0pF Typical
- RoHS Compliant
- SMT, TH, and Bare Die Package options.

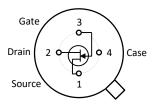
### **Applications**

- Mixers
- Oscillators
- VHF Amplifiers
- · Small Signal Amplifiers

### Description

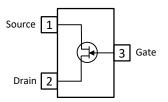
The -50V InterFET 2N4222 and 2N4222A are targeted for sensitive amplifier stages for midfrequencies designs. The "A" variants are screened for lower noise. The TO-72 package is hermetically sealed and suitable for military applications.

#### **TO-72 Bottom View**



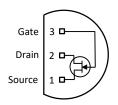


#### **SOT23 Top View**





#### **TO-92 Bottom View**





#### **Product Summary**

	Parameters	2N4222 Min	2N4222A Min	Unit
$BV_GSS$	Gate to Source Breakdown Voltage	-30	-30	V
I <sub>DSS</sub>	Drain to Source Saturation Current	5	5	mA
V <sub>GS(off)</sub>	Gate to Source Cutoff Voltage			V
G <sub>FS</sub>	Forward Transconductance	2500	2500	μS

### Ordering Information Custom Part and Binning Options Available

Part Number	Description	Case	Packaging
2N4222; 2N4222A	Through-Hole	TO-72	Bulk
PN4222; PN4222A	Through-Hole	TO-92	Bulk
SMP4222; SMP4222A	Surface Mount	SOT23	Bulk
	7" Tape and Reel: Max 3,000 Pieces		Minimum 1,000 Pieces
SMP4222TR; SMP4222ATR	13" Tape and Reel: Max 9,000 Pieces	SOT23	Tape and Reel
2N4222COT; 2N4222ACOT	Chip Orientated Tray (COT Waffle Pack)	СОТ	400/Waffle Pack
2N4222CFT; 2N4222ACFT	Chip Face-up Tray (CFT Waffle Pack)	CFT	400/Waffle Pack



**Disclaimer:** It is the Buyers responsibility for designing, validating and testing the end application under all field use cases and extreme use conditions. Guaranteeing the application meets required standards, regulatory compliance, and all safety and security requirements is the responsibility of the Buyer. These resources are subject to change without notice.









### **Electrical Characteristics**

Maximum Ratings (@ T<sub>A</sub> = 25°C, Unless otherwise specified)

	Parameters	Value	Unit		
$V_{\text{RGS}}$	Reverse Gate Source and Gate Drain Voltage	-30	V		
I <sub>FG</sub>	Continuous Forward Gate Current	10	mA		
PD	Continuous Device Power Dissipation	300	mW		
Р	Power Derating	2	mW/°C		
Tı	Operating Junction Temperature	-55 to 125	°C		
T <sub>STG</sub>	Storage Temperature	-65 to 150	°C		

Static Characteristics (@ TA = 25°C, Unless otherwise specified)

			2N4222		2N4222A		
	Parameters	Conditions	Min	Max	Min	Max	Unit
V <sub>(BR)GSS</sub>	Gate to Source Breakdown Voltage	$V_{DS} = 0V$ , $I_{G} = -1\mu A$	-30		-30		V
I <sub>GSS</sub>	Gate to Source	$V_{GS} = -15V$ , $V_{DS} = 0V$ , $T_A = 25$ °C		-0.1		-0.1	nA
	Reverse Current	$V_{GS} = -15V$ , $V_{DS} = 0V$ , $T_A = 150$ °C		-0.1		-0.1	μΑ
V <sub>GS</sub>	Gate Source Voltage	$V_{DS} = 15V, I_{D} = ()$	-2 (500)	-6 (500)	-2 (500)	-6 (500)	V μA
V <sub>GS(OFF)</sub>	Gate to Source Cutoff Voltage	V <sub>DS</sub> = 15V, I <sub>D</sub> = 0.1nA		-8		-8	V
I <sub>DSS</sub>	Drain to Source Saturation Current	$V_{GS} = 0V$ , $V_{DS} = 15V$ (Pulsed)	5	15	5	15	mA

**Dynamic Characteristics** (@ TA = 25°C, Unless otherwise specified)

			2N4222		2N4222A		
	Parameters	Conditions	Min	Max	Min	Max	Unit
GFS	Forward Transconductance	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1kHz	2500	6000	2500	6000	μS
Gos	Output Conductance	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1kHz		40		40	μS
Ciss	Input Capacitance	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1MHz		6		6	pF
Crss	Reverse Transfer Capacitance	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1MHz		2		2	pF
NF	Noise Figure	$V_{DS}$ = 15V, $V_{GS}$ = 0V, $f$ = 1kHz $R_G$ = 1 M $\Omega$				2.5	dB



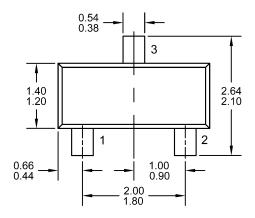


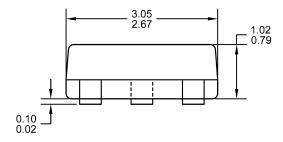




## SOT23 (TO-236AB) Mechanical and Layout Data

### **Package Outline Data**



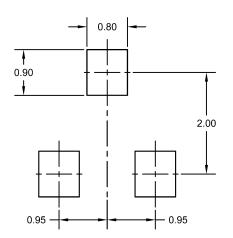


0.09 0.27 0.13 0.27 0.13

0.15

- 1. All linear dimensions are in millimeters.
- 2. Package weight approximately 0.12 grams
- 3. Molded plastic case UL 94V-0 rated
- For Tape and Reel specifications refer to InterFET CTC-021 Tape and Reel Specification, Document number: IF39002
- Bulk product is shipped in standard ESD shipping material
- 6. Refer to JEDEC standards for additional information.

### **Suggested Pad Layout**



- 1. All linear dimensions are in millimeters.
- The suggested land pattern dimensions have been provided for reference only. A more robust pattern may be desired for wave soldering.



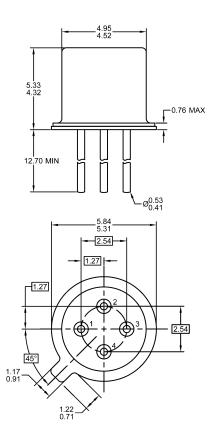






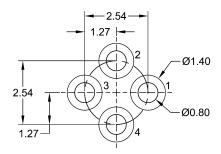
## **TO-72 Mechanical and Layout Data**

### **Package Outline Data**



- 1. All linear dimensions are in millimeters.
- Four leaded device. Not all leads are shown in drawing views.
- 3. Package weight approximately 0.31 grams
- Bulk product is shipped in standard ESD shipping material
- 5. Refer to JEDEC standards for additional information.

### **Suggested Through-Hole Layout**



- 1. All linear dimensions are in millimeters.
- The suggested land pattern dimensions have been provided as a straight lead reference only. A more robust pattern may be desired for wave soldering and/or bent lead configurations.



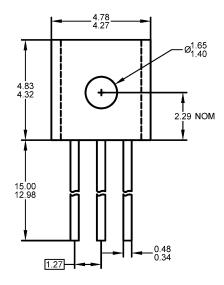


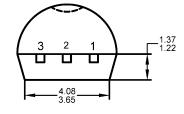


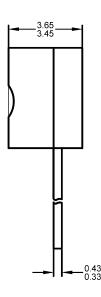


### **TO-92 Mechanical and Layout Data**

### **Package Outline Data**

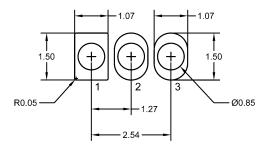






- 1. All linear dimensions are in millimeters.
- 2. Package weight approximately 0.19 grams
- 3. Molded plastic case UL 94V-0 rated
- Bulk product is shipped in standard ESD shipping material
- 5. Refer to JEDEC standards for additional information.

### **Suggested Through-Hole Layout**



- 1. All linear dimensions are in millimeters.
- The suggested land pattern dimensions have been provided as a straight lead reference only. A more robust pattern may be desired for wave soldering and/or bent lead configurations.

# **Mouser Electronics**

**Authorized Distributor** 

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InterFET:

2N4222A 2N4222 SMP4222